

# IRFIZ24V

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Optimized for SMPS Applications

## Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

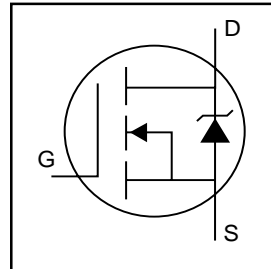
The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.

## Absolute Maximum Ratings

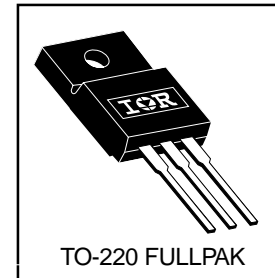
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	14	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	10	
$I_{DM}$	Pulsed Drain Current ①	68	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	26	W
	Linear Derating Factor	0.18	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_{AR}$	Avalanche Current ①	17	A
$E_{AR}$	Repetitive Avalanche Energy ①	4.4	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.2	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

## Thermal Resistance

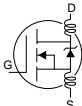
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	5.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	62	



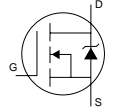
$V_{DSS} = 60\text{V}$
$R_{DS(on)} = 0.060\Omega$
$I_D = 14\text{A}$



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.06	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	60	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	7.8	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 10A④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	23	nC	I <sub>D</sub> = 17A ⑦
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	7.7		V <sub>DS</sub> = 48V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	6.2		V <sub>GS</sub> = 10V, See Fig. 6 and 13
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.6	—	ns	V <sub>DD</sub> = 30V
t <sub>r</sub>	Rise Time	—	46	—		I <sub>D</sub> = 17A ⑦
t <sub>d(off)</sub>	Turn-Off Delay Time	—	21	—		R <sub>G</sub> = 18Ω
t <sub>f</sub>	Fall Time	—	24	—		V <sub>GS</sub> = 10V, See Fig. 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	590	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	140	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	23	—		f = 1.0MHz, See Fig. 5
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	140⑤	43⑥		mJ

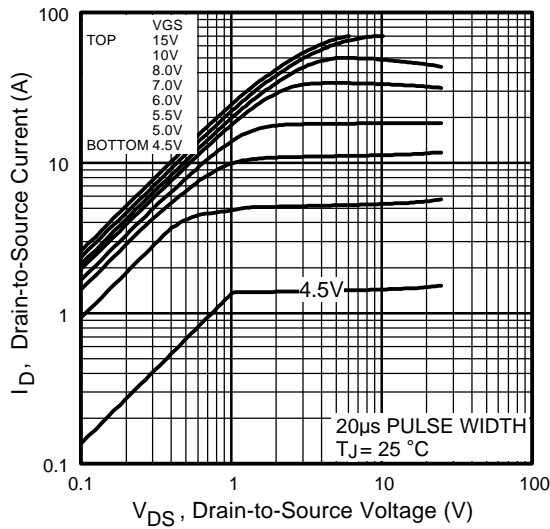
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	14	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode)①	—	—	68		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 17A ⑦, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	53	79	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 17A ⑦
Q <sub>rr</sub>	Reverse Recovery Charge	—	90	130	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

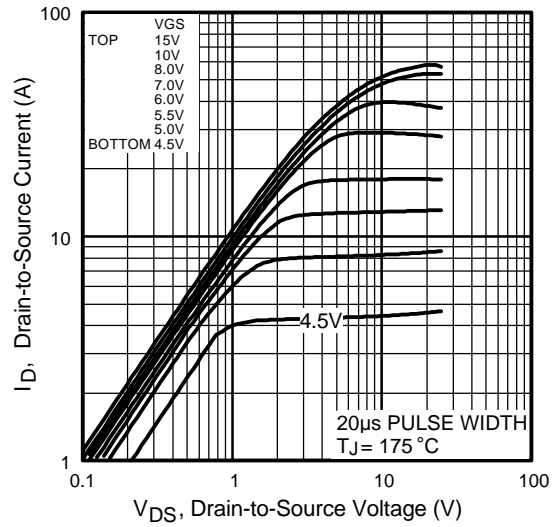
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting T<sub>J</sub> = 25°C, L = 300μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 14A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 14A, di/dt ≤ 240A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C

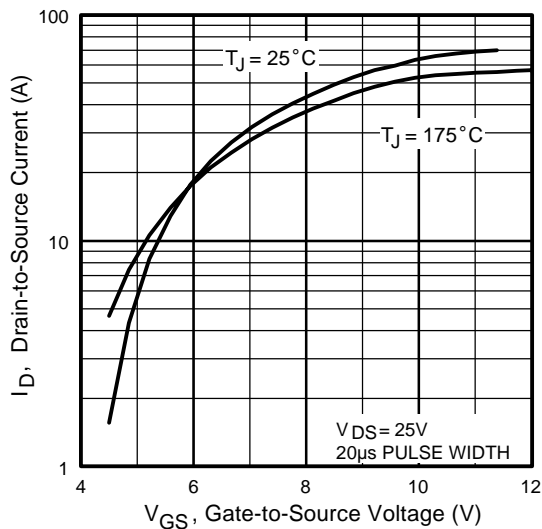
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- ⑥ This is a calculated value limited to T<sub>J</sub> = 175°C .
- ⑦ I<sub>D</sub> = 17A is copied from TO-220 device.



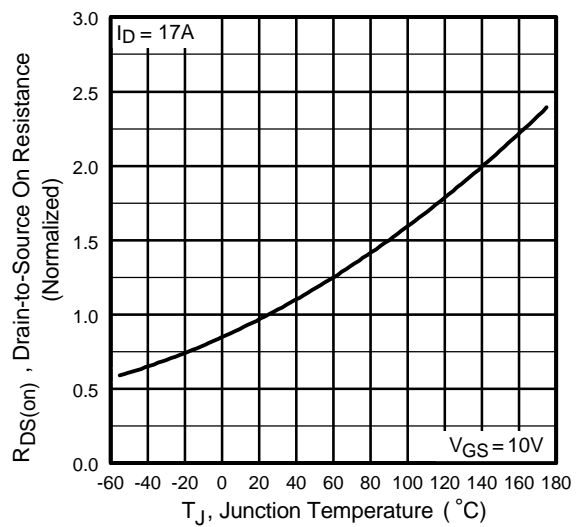
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



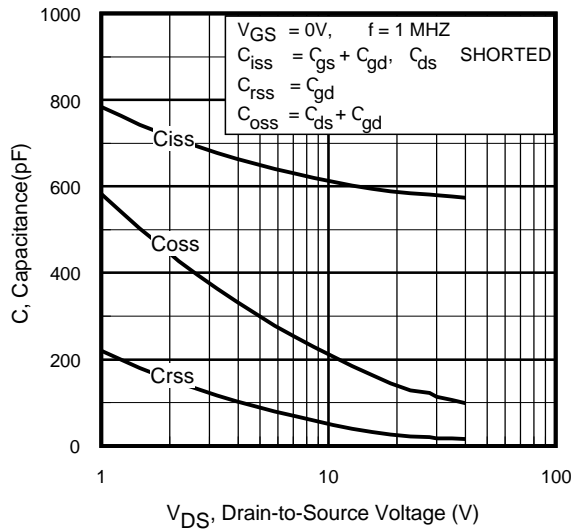
**Fig 3.** Typical Transfer Characteristics



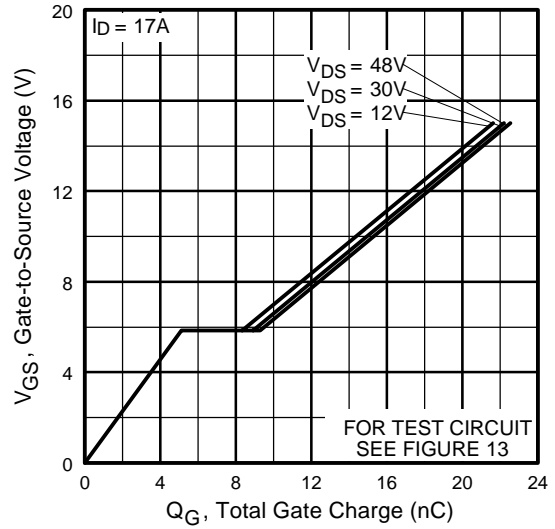
**Fig 4.** Normalized On-Resistance Vs. Temperature

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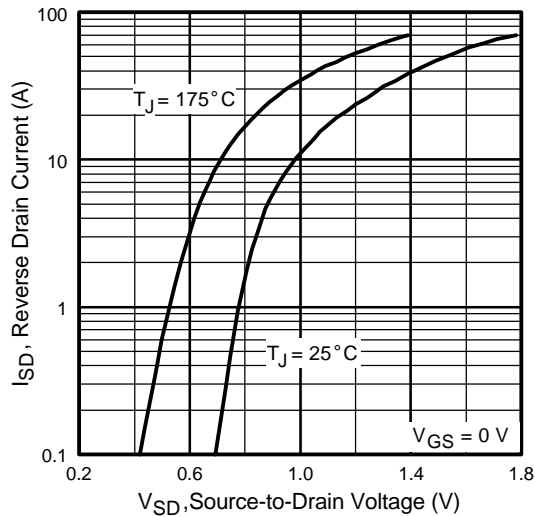
International  
**IR** Rectifier



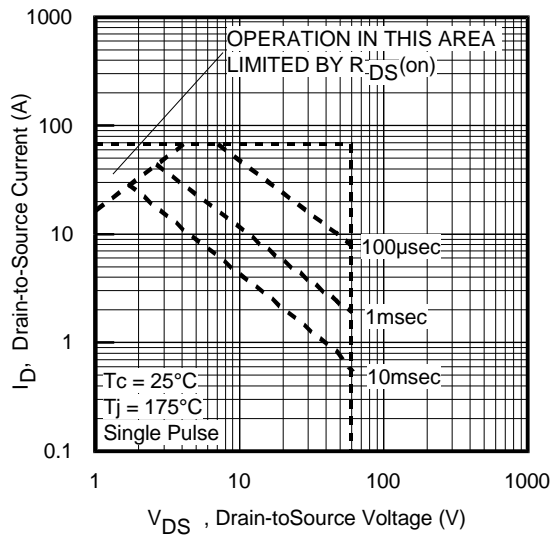
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



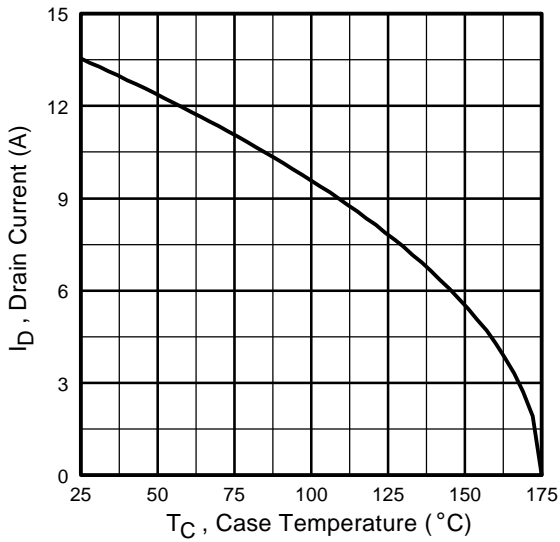
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



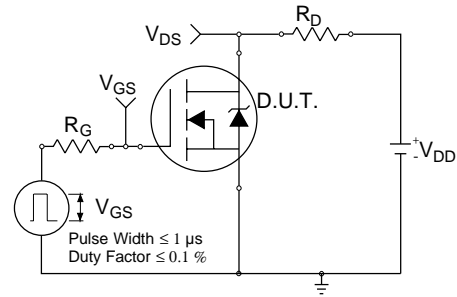
**Fig 7.** Typical Source-Drain Diode Forward Voltage



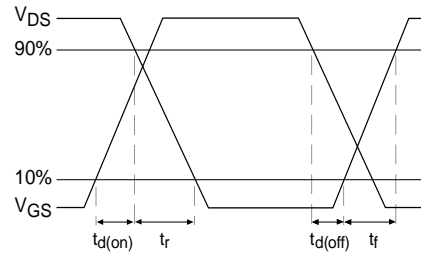
**Fig 8.** Maximum Safe Operating Area



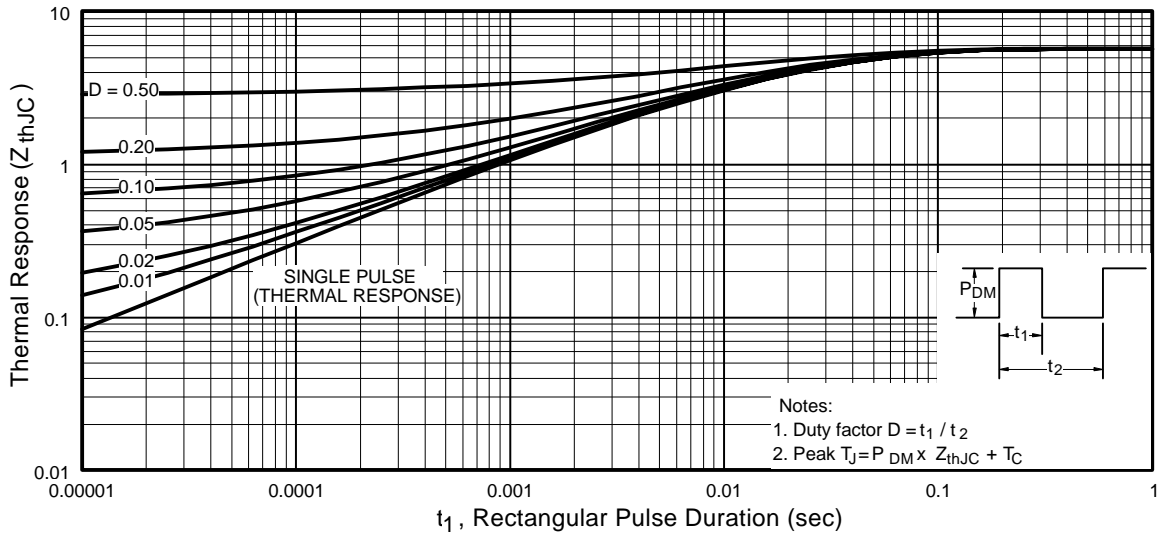
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

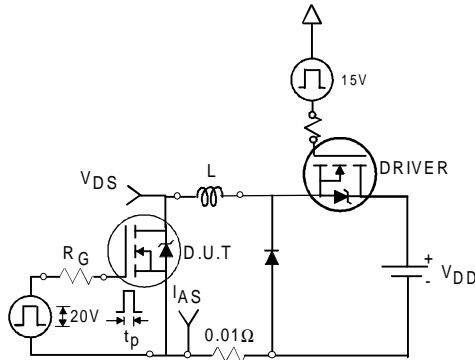


**Fig 10b.** Switching Time Waveforms

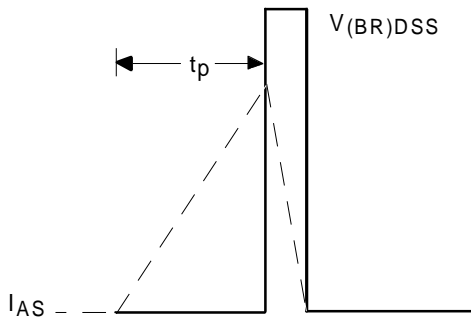


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

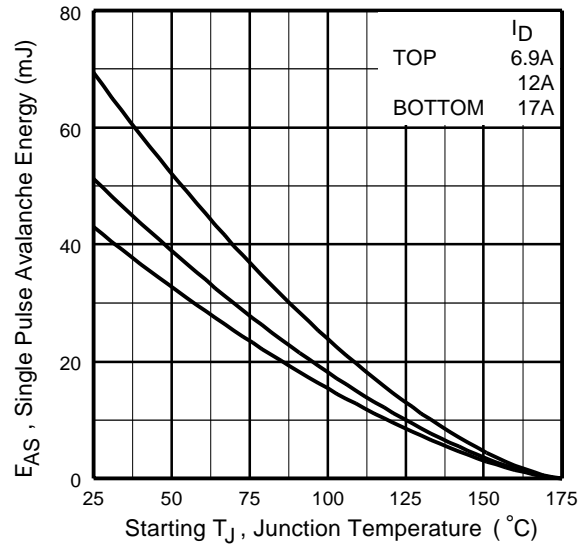
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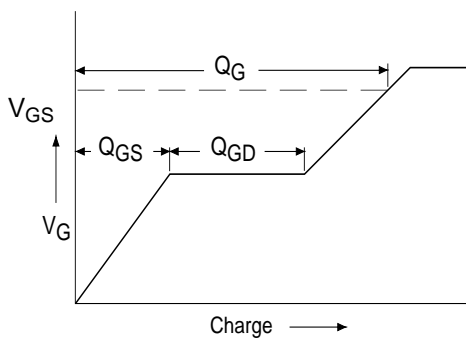
**Fig 12a.** Unclamped Inductive Test Circuit



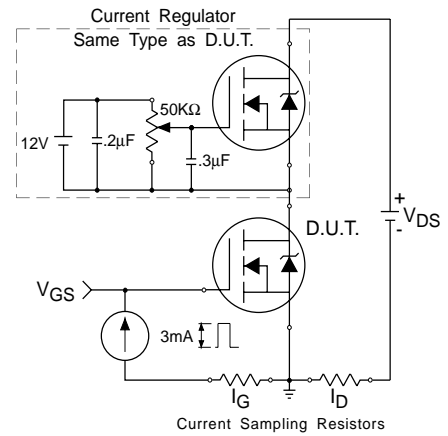
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

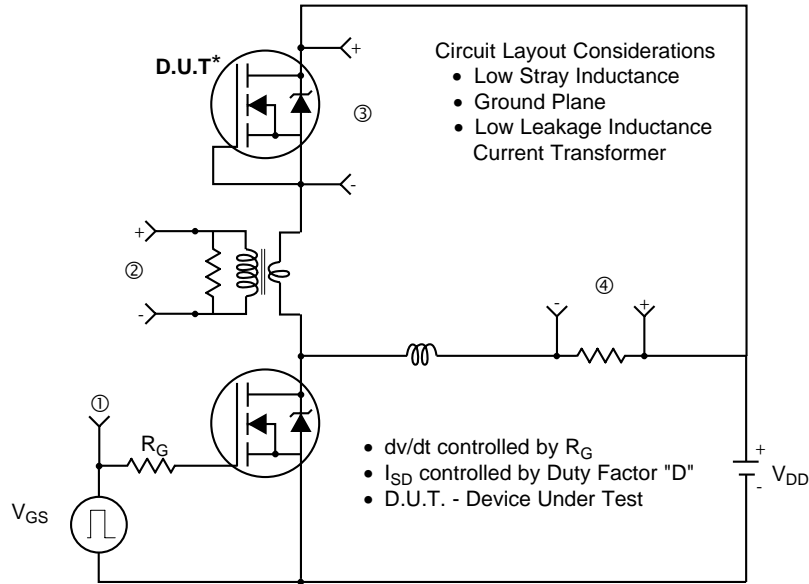


**Fig 13a.** Basic Gate Charge Waveform

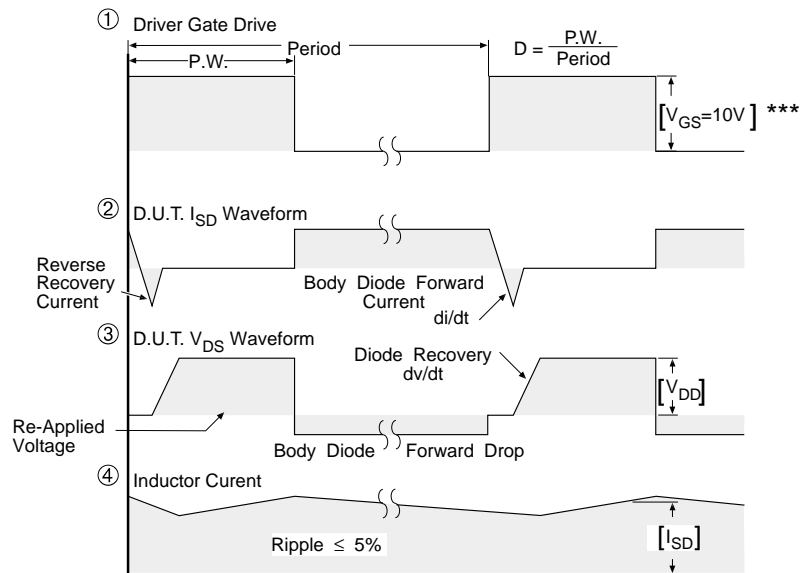


**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\* Reverse Polarity of D.U.T for P-Channel



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

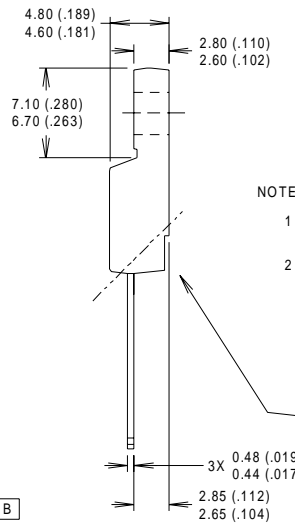
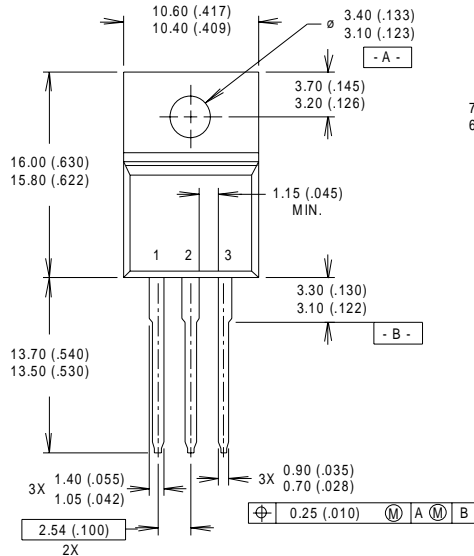
**Fig 14.** For N-channel HEXFET® power MOSFETs

# IRFIZ24V

International  
**IR** Rectifier

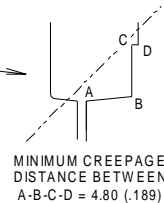
## Package Outline TO-220 Fullpak Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS  
1 - GATE  
2 - DRAIN  
3 - SOURCE

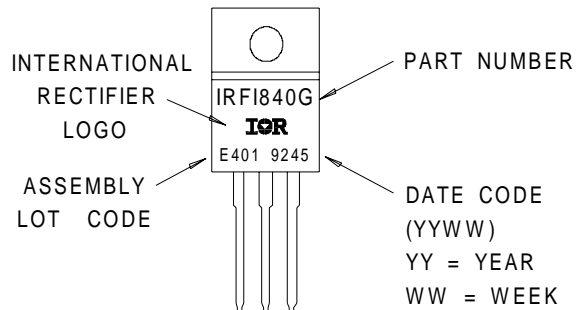
NOTES:  
1 DIMENSIONING & TOLERANCING  
PER ANSI Y14.5M, 1982  
2 CONTROLLING DIMENSION: INCH.



## Part Marking Information

### TO-220 Fullpak

EXAMPLE : THIS IS AN IRFI840G  
WITH ASSEMBLY  
LOT CODE E401



Data and specifications subject to change without notice.  
This product has been designed and qualified for the industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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